HIGH-SPEED CMOS OCTAL BUFFER/LINE DRIVER

IDT54/74AHCT244
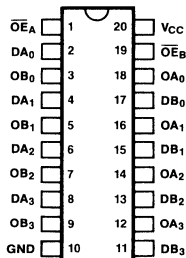
Integrated Device Technology, Inc.

FEATURES:

- Equivalent to ALS speeds and output drive over full temperature and voltage supply extremes
- 7ns typical data to output delay
- I_{OL} = 14mA over full military temperature range
- CMOS power levels (5μW typ. static)
- Both CMOS and TTL output compatible
- Substantially lower input current levels than ALS (5μA max.)
- Octal buffer/line driver with 3-state output
- 100% product assurance screening to MIL-STD-883, Class B is available
- JEDEC standard pinout for DIP and LCC

DESCRIPTION:

The IDT54/74AHCT244 are octal buffer/line drivers built using advanced CEMOS™, a dual metal CMOS technology. The devices are designed to be employed as memory and address drivers, clock drivers and bus-oriented transmitters/receivers which provide improved board density.

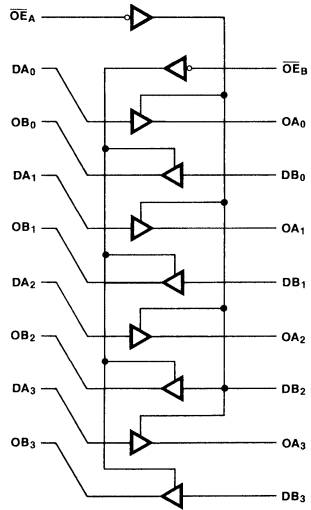## PIN CONFIGURATIONS

SSD54/74AHCT244-001

DIP
TOP VIEW
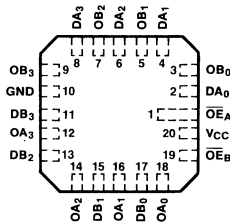
SSD54/74AHCT244-002

LCC
TOP VIEW

FUNCTIONAL BLOCK DIAGRAM

SSD54/74AHCT244-003

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MILITARY AND COMMERCIAL TEMPERATURE RANGES

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ABSOLUTE MAXIMUM RATING[1]

SYMBOL	RATING	COMMERCIAL	MILITARY	UNIT
V_{TERM}	Terminal Voltage with Respect to GND	–0.5 to +7.0	–0.5 to +7.0	V
T_A	Operating Temperature	0 to +70	–55 to +125	°C
T_{BIAS}	Temperature Under Bias	–55 to +125	–65 to +135	°C
T_{STG}	Storage Temperature	–55 to +125	–65 to +155	°C
I_{OUT}	DC Output Current	120	120	mA

NOTE:

1. Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

DC ELECTRICAL CHARACTERISTICS OVER OPERATING RANGE

Following Conditions Apply Unless Otherwise Specified:

T_A = 0°C to +70°C V_{CC} = 5.0V ± 5%   Min. = 4.75V   Max. = 5.25V (Commercial)

T_A = –55°C to +125°C V_{CC} = 5.0V ± 10%   Min. = 4.50V   Max. = 5.50V (Military)

V_{LC} = 0.2V

V_{HC} = V_{CC} – 0.2V

SYMBOL	PARAMETER	TEST CONDITIONS[1]			MIN.	TYP.[2]	MAX.	UNIT
V_{IH}	Input HIGH Level	Guaranteed Logic High Level			2.0	—	—	V
V_{IL}	Input LOW Level	Guaranteed Logic Low Level			—	—	0.8	V
I_{IH}	Input HIGH Current	V_{CC} = Max., V_{IN} = V_{CC}			—	—	5	μA
I_{IL}	Input LOW Current	V_{CC} = Max., V_{IN} = GND			—	—	–5	μA
I_{SC}	Short Circuit Current	V_{CC} = Max.[3]			–60	–100	—	mA
V_{OH}	Output HIGH Voltage	V_{CC} = 3V, V_{IN} = V_{LC} or V_{HC}, I_{OH} = –32μA			V_{HC}	V_{CC}	—	V
		V_{CC} = Min. V_{IN} = V_{IH} or V_{IL}	I_{OH} = –150μA		V_{HC}	V_{CC}	—	
			I_{OH} = –12mA MIL		2.4	4.3	—	
			I_{OH} = –15mA COM		2.4	4.3	—	
V_{OL}	Output LOW Voltage	V_{CC} = 3V, V_{IN} = V_{LC} or V_{HC}, I_{OL} = 300μA			—	GND	V_{LC}	V
		V_{CC} = Min. V_{IN} = V_{IH} or V_{IL}	I_{OL} = 300μA		—	GND	V_{LC}	
			I_{OL} = 14mA MIL		—	—	0.4	
			I_{OL} = 24mA COM		—	—	0.5	

NOTES:

1. For conditions shown as max. or min., use appropriate value specified under Electrical Characteristics for the applicable device type.

2. Typical values are at V_{CC} = 5.0V, +25°C ambient and maximum loading.

3. Not more than one output should be shorted at one time. Duration of the short circuit test should not exceed one second.

POWER SUPPLY CHARACTERISTICS

$V_{LC} = 0.2V$; $V_{HC} = V_{CC} - 0.2V$

SYMBOL	PARAMETER	TEST CONDITIONS[1]		MIN.	TYP.[2]	MAX.	UNIT
I_{CCQ}	Quiescent Power Supply Current	V_{CC} = Max. $V_{IN} \geq V_{HC}$; $V_{IN} \leq V_{LC}$ $f_i = 0$		—	0.001	1.5	mA
I_{CCT}	Power Supply Current Per TTL Inputs HIGH	V_{CC} = Max. $V_{IN} = 3.4V$[3]		—	0.5	1.6	mA
I_{CCD}	Dynamic Power Supply Current	V_{CC} = Max. Outputs Open $\overline{OE}_A = \overline{OE}_B$ = GND One Input Toggling 50% Duty Cycle	$V_{IN} \geq V_{HC}$ $V_{IN} \leq V_{LC}$	—	0.15	0.25	mA/ MHz
I_{CC}	Total Power Supply[4] Current	V_{CC} = Max. Outputs Open f_i = 1.0MHz 50% Duty Cycle $\overline{OE}_A = \overline{OE}_B$ = GND One Bit Toggling	$V_{IN} \geq V_{HC}$ $V_{IN} \leq V_{LC}$ (AHCT)	—	0.15	1.8	mA
			V_{IN} = 3.4V or V_{IN} = GND	—	0.4	2.6	
		V_{CC} = Max. Outputs Open f_i = 250kHz 50% Duty Cycle $\overline{OE}_A = \overline{OE}_B$ = GND Eight Bits Toggling	$V_{IN} \geq V_{HC}$ $V_{IN} \leq V_{LC}$ (AHCT)	—	0.3	2.0	
			V_{IN} = 3.4V or V_{IN} = GND	—	2.3	8.4	

NOTES:

1. For conditions shown as max. or min., use appropriate value specified under Electrical Characteristics for the applicable device type.

2. Typical values are at V_{CC} = 5.0V, +25°C ambient and maximum loading.

3. Per TTL driven input (V_{IN} = 3.4V); all other inputs at V_{CC} or GND.

4. $I_{CC} = I_{QUIESCENT} + I_{INPUTS} + I_{DYNAMIC}$

   $I_{CC} = I_{CCQ} + I_{CCT}D_H N_T + I_{CCD} (f_{CP}/2 + f_i N_i)$

   I_{CCQ} = Quiescent Current

   I_{CCT} = Power Supply Current for a TTL High Input (V_{IN} = 3.4V)

   D_H = Duty Cycle for TTL Inputs High

   N_T = Number of TTL Inputs at D_H

   I_{CCD} = Dynamic Current caused by an Input Transition pair (HLH or LHL)

   f_{CP} = Clock Frequency for Register Devices (Zero for Non-Register Devices)

   f_i = Input Frequency

   N_i = Number of Inputs at f_i

   All currents are in milliamps and all frequencies are in megahertz.

DEFINITION OF FUNCTIONAL TERMS

PIN NAMES	DESCRIPTION
$\overline{OE}_A$, $\overline{OE}_B$	3-State Output Enable Input (Active LOW)
Dxx	Inputs
Oxx	Outputs

TRUTH TABLE

INPUTS		OUTPUT
$\overline{OE}_A$, $\overline{OE}_B$	D	
L	L	L
L	H	H
H	X	Z

H = HIGH Voltage Level
L = LOW Voltage Level
X = Don't Care
Z = High Impedance

SWITCHING CHARACTERISTICS OVER OPERATING RANGE

SYMBOL	PARAMETER	CONDITION	TYPICAL	COMMERCIAL		MILITARY		UNITS
				MIN.	MAX.	MIN.	MAX.	
t_{PLH} t_{PHL}	Propagation Delay D_N to O_N		7.0	3.0	10.0	3.0	13.0	ns
t_{ZH} t_{ZL}	Output Enable Time	C_L = 50pf R_L = 500Ω	16.0	7.0	20.0	7.0	25.0	ns
t_{HZ} t_{LZ}	Output Disable Time		10.0	2.0	13.0	2.0	18.0	ns